

10/659,778

FIS919990263US2

CLAIM AMENDMENTS

20. (Currently Amended) A metallization insulating structure, comprising:
- a substrate having ~~metal structures~~ wires therein;
 - a first layer, the first layer a substantially fluorine free insulating layer formed on the substrate, having a height, h_i ;
 - a second layer, the second layer a fluorine containing insulating layer formed directly on the first layer, having a height h_f ;
 - a metal structure of at least height $h_i + h_f$ formed in the first and second layer, the metal structure extending to ~~the~~ a substantially planar substrate.
21. (Previously Presented) The metallization insulating structure of claim 20 further comprising a capping layer on the substrate, underlying the first layer.
22. (Previously Presented) The metallization insulating structure according to claim 20 wherein the fluorine containing insulating layer comprises a material selected from the group consisting of fluorinated silicon oxide, fluorinated amorphous carbon, fluorinated diamondlike carbon and fluorinated organic polymers.
23. (Previously Presented) The metallization insulating structure according to claim 20 wherein the substantially fluorine free insulating layer comprises undoped silicon glass.
24. (Previously presented) The metallization insulating structure according to claim 21 wherein the capping layer comprises a material selected from the group consisting of silicon nitride, silicon carbide and hydrogenated silicon carbide, or combinations thereof.

Claims 25-26 (Cancelled)

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27. (Previously presented) The metallization structure of claim 21 wherein the metal structure extends through the capping layer such that the height of the structure is greater than $h_i + h_f$.

Claim 28 (Canceled)

29. (Currently Amended) The structure of claim 21 wherein the metal structure is in contact with the underlying ~~metal structures~~ wires through the capping layer.